

# Schottky Diode Gen<sup>2</sup>

$$V_{RRM} = 100\text{ V}$$

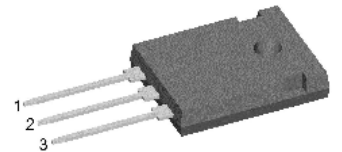
$$I_{FAV} = 2 \times 25\text{ A}$$

$$V_F = 0.72\text{ V}$$

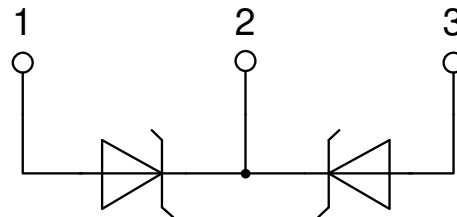
High Performance Schottky Diode  
 Low Loss and Soft Recovery  
 Common Cathode

Part number

**DSA50C100HB**



Backside: cathode



### Features / Advantages:

- Very low  $V_f$
- Extremely low switching losses
- Low  $I_{rm}$  values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

### Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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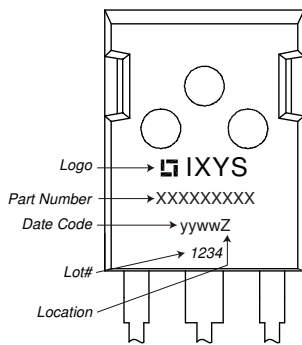


Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					100	V
$V_{RRM}$	max. repetitive reverse blocking voltage					100	V
$I_R$	reverse current, drain current	$V_R = 100\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		450	$\mu\text{A}$
		$V_R = 100\text{ V}$		$T_{VJ} = 125^\circ\text{C}$		5	mA
$V_F$	forward voltage drop	$I_F = 25\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		0.90	V
		$I_F = 50\text{ A}$				1.07	V
		$I_F = 25\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0.72	V
		$I_F = 50\text{ A}$				0.90	V
$I_{FAV}$	average forward current	$T_C = 155^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		25	A
$V_{F0}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.45	V
$r_F$	slope resistance					7.3	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.95	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.3		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		160	W
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		440	A
$C_J$	junction capacitance	$V_R = 12\text{ V}$	$f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		289	pF



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			50	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

- D = Diode
- S = Schottky Diode
- A = low VF
- 50 = Current Rating [A]
- C = Common Cathode
- 100 = Reverse Voltage [V]
- HB = TO-247AD (3)

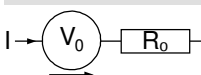
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA50C100HB	DSA50C100HB	Tube	30	502774

Similar Part	Package	Voltage class
DSA50C100QB	TO-3P (3)	100
DSA60C100PB	TO-220AB (3)	100

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 175^{\circ}C$

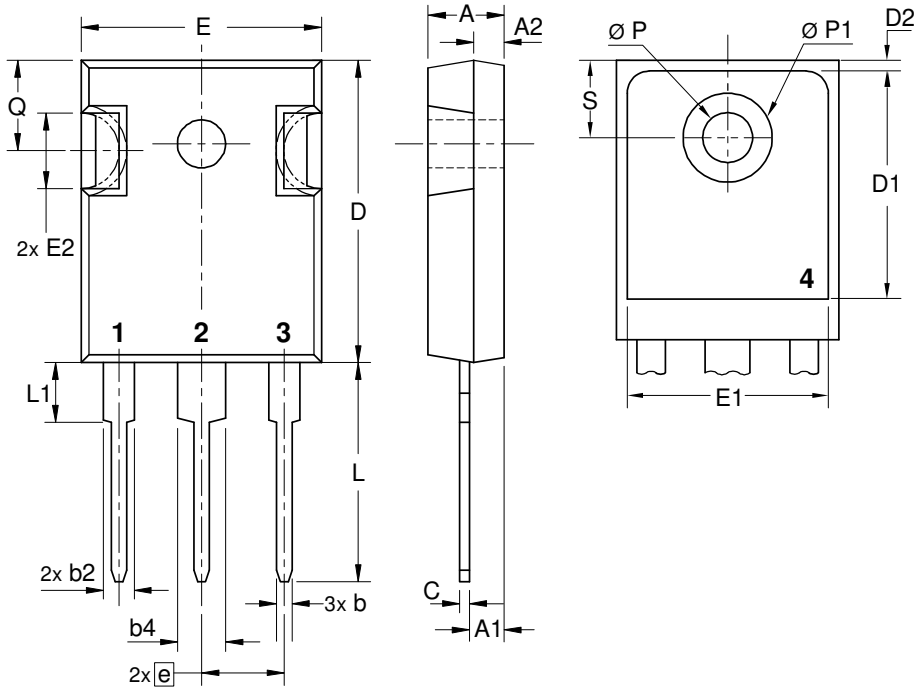


**Schottky**

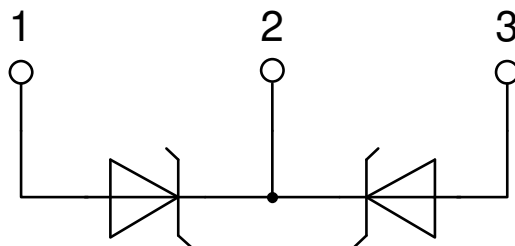
$V_{0\ max}$	threshold voltage	0.45	V
$R_{0\ max}$	slope resistance *	4.7	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39





**Schottky**

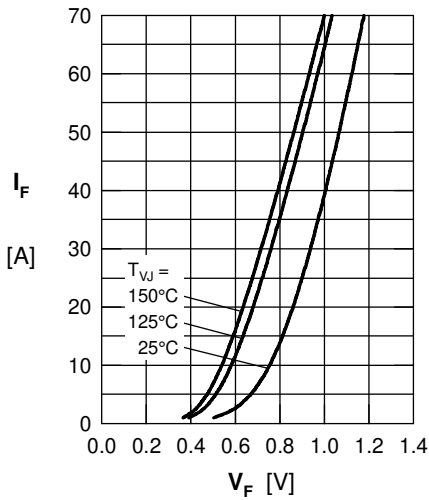


Fig. 1 Maximum forward voltage drop characteristics

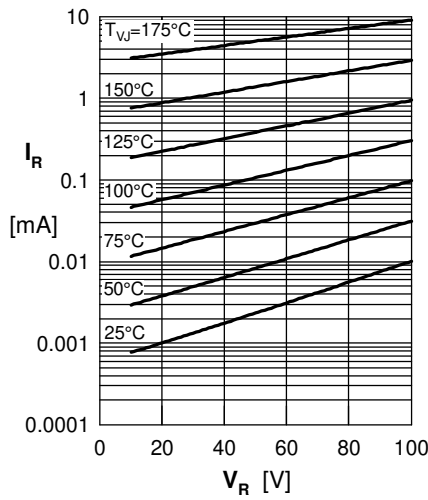


Fig. 2 Typ. reverse current  $I_R$  vs. reverse voltage  $V_R$

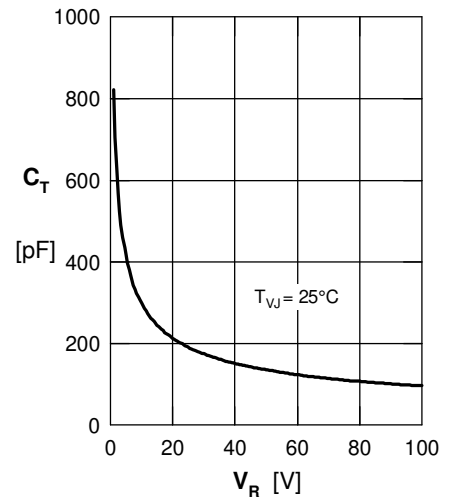


Fig. 3 Typ. junction capacitance  $C_T$  vs. reverse voltage  $V_R$

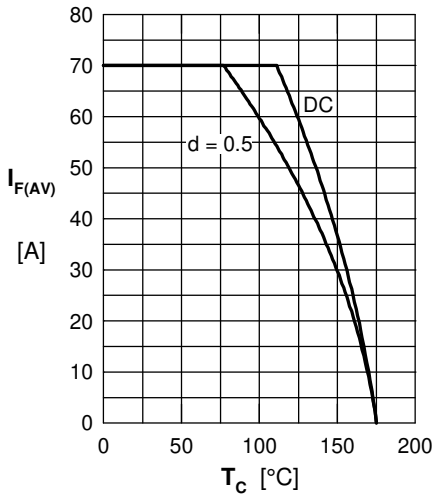


Fig. 4 Average forward current  $I_{F(AV)}$  vs. case temperature  $T_C$

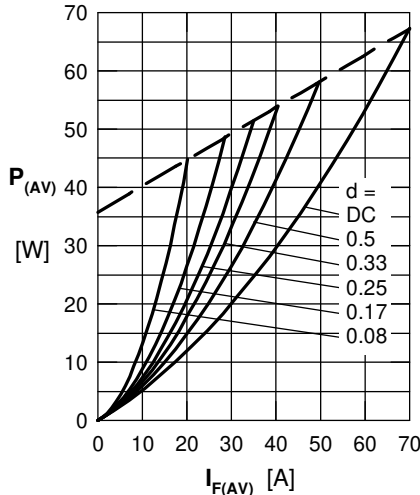


Fig. 5 Forward power loss characteristics

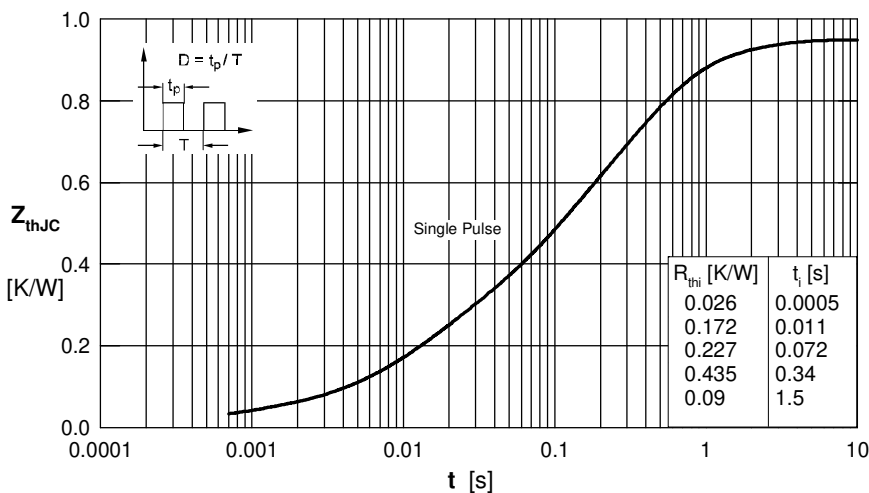


Fig. 6 Transient thermal impedance junction to case

Note: All curves are per diode